

Phototransistor chip FT060-02

Description

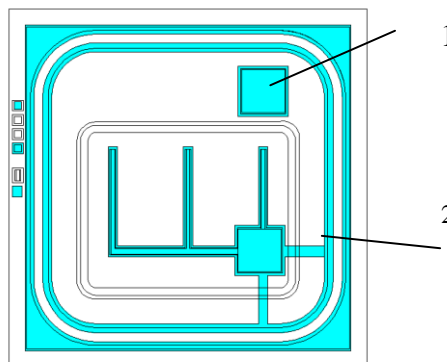
FT060-02 chip is designed to be used in transistor optocouplers, hybrid microcircuits and packaged phototransistors.

Features

- High Current Transfer Ratio
- Chip size - 1.0 x 1.0 mm
- Chip thickness - 0.36 mm±0.02mm
- Contact pads size:
Base - 0.12 mm x 0.12 mm
Emitter - 0.12 mm x 0.12 mm
- Metallization: top - Al
bottom (Collector) - CrAu for bonding on conductive adhesive

Absolute maximum ratings

Operating junction temperature	-55°C to 110°C
Limiting temperature	-60°C to 150°C



1 - Base
2 - Emitter

Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Collector-Emitter Breakdown Voltage	BV_{CEOL}	60	-	-	V	$I_{CE}=10\text{ mA}$
Collector-Emitter Leakage Current	$I_{LEAK\ CE}$	-	-	1.0	μA	$V_{CE}=75\text{ V}$
Emitter-Base Current	I_{CE0}	-	-	1.0	μA	$V_{EB}=5\text{ V}$
Collector-Emitter Saturation Voltage	$V_{CE\ SAT}$	-	-	0.2	V	$I_B=35\ \mu\text{A}, I_C=10\text{ mA}$
Current Transfer Ratio	h_{21E}	400	-	1 100	-	$V_{CE}=10\text{ V}, I_B=35\ \mu\text{A}$